

FABRICATING DEEPER AND SHALLOWER
TRENCHES IN A SEMICONDUCTOR STRUCTURE

Abstract of the Disclosure

Crossing trenches of different depths may be formed in the same semiconductor structure by etching the deeper trench first. The deeper trench and the substrate may then
5 be covered with a material that prevents further etching. The covering is etched through for the shallower trench, leaving a protective covering in the deeper trench.